





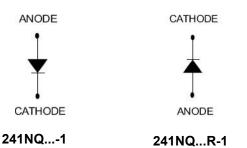
241NQ035(R)-1/241NQ040(R)-1/241NQ045(R)-1 SCHOTTKY RECTIFIER



Features

- 175℃ T_J operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5' S
- Easier to mount and lower profile than DO-5' S
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Baseplate: Nickel plated; Terminals: Nickel plated
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Repetitive Reverse Voltage	V_{RRM}	-	35	241NQ035(R)-1	
Working Peak Reverse Voltage	V_{RWM}		40 241NQ040(R)-1		V
DC Blocking Voltage	V_R		45	241NQ045(R)-1	
Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =96°C, rectangular wave form	240		А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse		4140	Α
Non-Repetitive Avalanche Energy	E _{AS}	T _J =25℃,I _{AS} =48A,L=0.28 mH	324		mJ
Repetitive Avalanche Current	I _{AR}	Current decaying linearly to zero in 1 µsec Frequency limited by T _J max. V _A =1.5×V _R typical	48		А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	\/	@ 240A, Pulse, T _J = 25 °C	0.59	0.69	V
	V_{F1}	@ 480A, Pulse, T _J = 25 °C	0.70	0.82	V
	V_{F2}	@ 240A, Pulse, T _J = 125 °C	0.53	0.59	V
	V F2	@ 480A, Pulse, T _J = 125 °C	0.62	0.72	V
Reverse Current*	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.2	20	mA
	I _{R2}	$@V_R = \text{rated } V_R T_J = 125 ^{\circ}\text{C}$	100	180	mA
Junction Capacitance	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	8600	10300	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $^{^{\}star}\,$ Pulse width < 300 $\mu s,\,$ duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specifica	Units	
Junction Temperature	TJ	-	-55 to +175		°C
Storage Temperature	T _{stg}	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.20		°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.15		°C/W
Mounting Torque	T _M	Non-lubricated threads	Mounting Torque Terminal Torque	23(min) 29(max) 35(min) 46(max)	Kg-cm
Approximate Weight	wt	-	25.6		g
Case Style	PRM1-1				

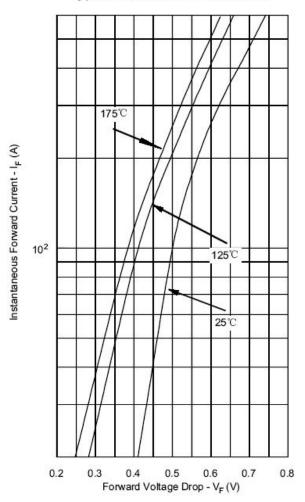




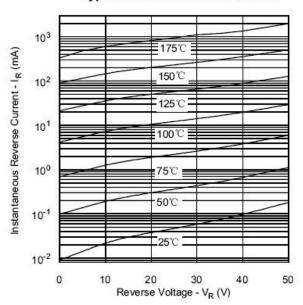


Ratings and Characteristics Curves

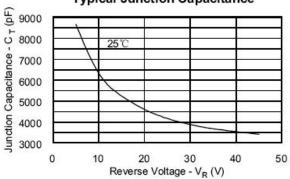
Typical Forward Characteristics



Typical Reverse Characteristics







Ordering Information

Device Package		Shipping		
241NQ1	PRM1-1(Pb-Free)	27pcs/box		

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXX is YYWW

1st row SS YYWW
2nd row 241NQ035-1
SS = SS
YY = Year
WW = Week

Cautions: Molding resin

Epoxy resin UL:94V-0

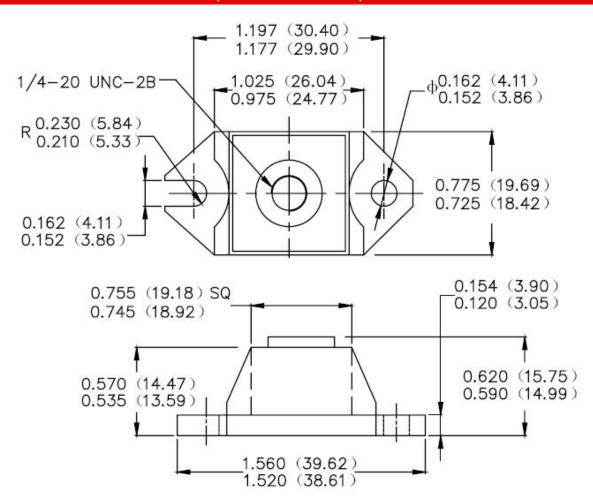
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Mechanical Dimensions PRM1-1 (Inches/Millimeters)



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